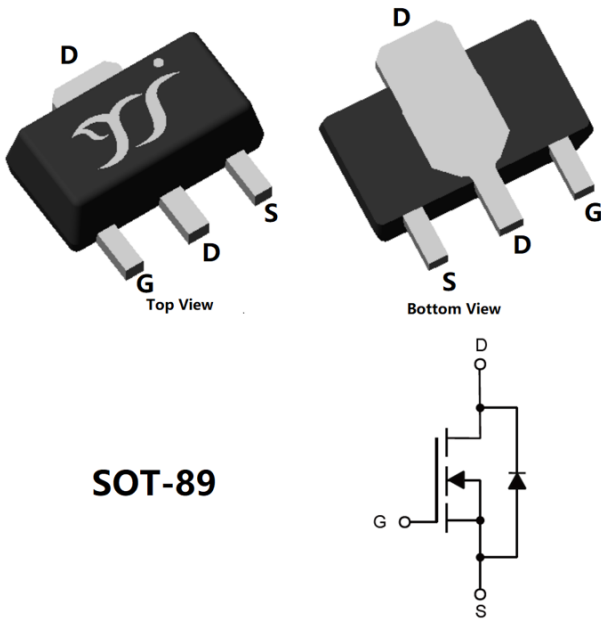


## N-Channel Enhancement Mode Field Effect Transistor



**SOT-89**

### Product Summary

- $V_{DS}$  60V
- $I_D$  3.0A
- $R_{DS(ON)}$ ( at  $V_{GS}=10V$ ) < 100mohm
- $R_{DS(ON)}$ ( at  $V_{GS}=4.5V$ ) < 120mohm

### General Description

- Trench Power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low  $R_{DS(ON)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

### Applications

- DC-DC Converters
- Power management functions

### ■ Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	$V_{DS}$	60	V
Gate-source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current	$I_D$	$T_A=25^\circ\text{C}$	3
		$T_A=70^\circ\text{C}$	2.4
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	12	A
Total Power Dissipation	$P_D$	$T_A=25^\circ\text{C}$	0.69
		$T_A=70^\circ\text{C}$	0.44
Thermal Resistance Junction-to-Ambient <sup>B</sup>	$R_{\theta JA}$	180	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ\text{C}$

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJH03N06A	F2	6003A	1000	8000	32000	7" reel



# YJH03N06A

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS1</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
	I <sub>GSS2</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V			±50	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.3	2.0	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3A		86	100	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A		92	120	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =3A, V <sub>GS</sub> =0V			1.2	V
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHZ		409		pF
Output Capacitance	C <sub>oss</sub>			50		
Reverse Transfer Capacitance	C <sub>rss</sub>			41		
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, I <sub>D</sub> =3A		10.27		nC
Gate-Source Charge	Q <sub>gs</sub>			1.65		
Gate-Drain Charge	Q <sub>gd</sub>			2.11		
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =3A, di/dt=100A/us		6.99		ns
Reverse Recovery Time	t <sub>rr</sub>			32.6		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, R <sub>L</sub> =20Ω R <sub>GEN</sub> =3Ω		3.6		ns
Turn-on Rise Time	t <sub>r</sub>			17.6		
Turn-off Delay Time	t <sub>D(off)</sub>			13		
Turn-off fall Time	t <sub>f</sub>			23		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design, while R<sub>θJA</sub> is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.



■ Typical Performance Characteristics

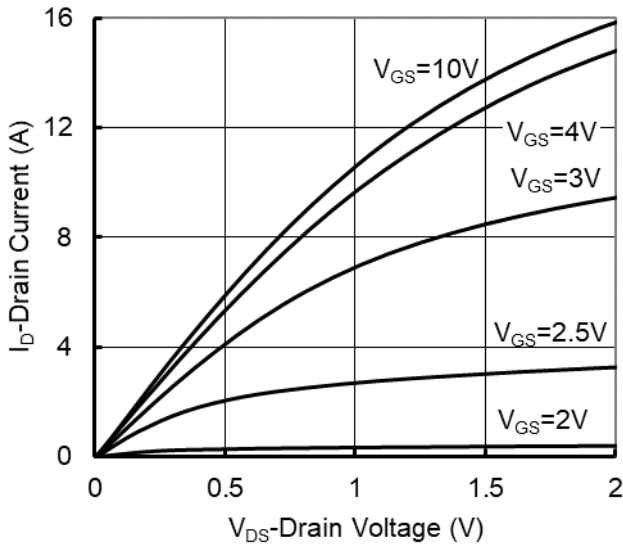


Figure1. Output Characteristics

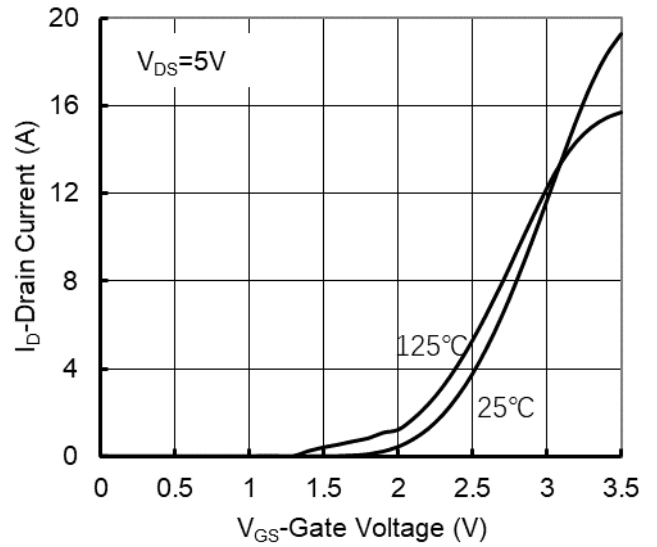


Figure2. Transfer Characteristics

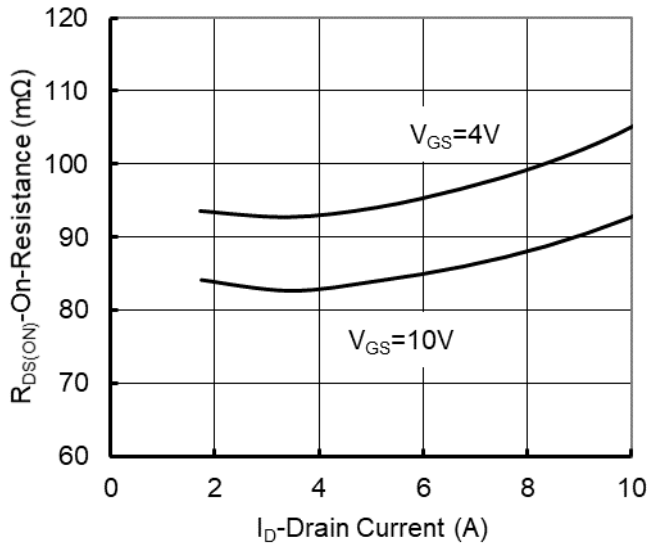


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

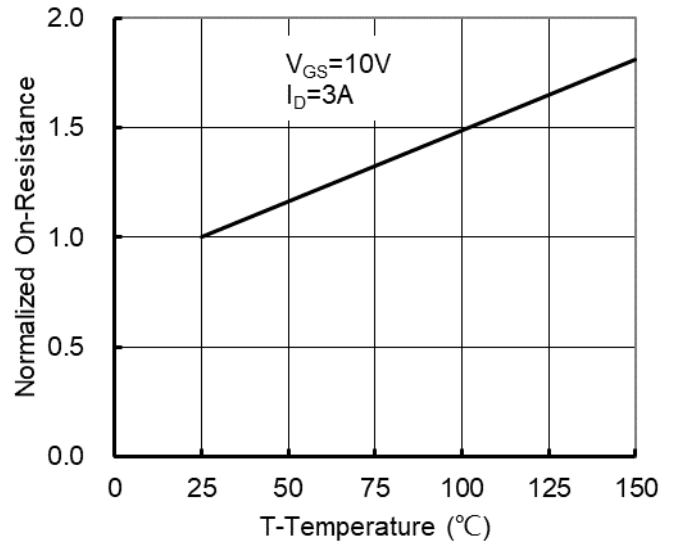


Figure 4: On-Resistance vs. Junction Temperature

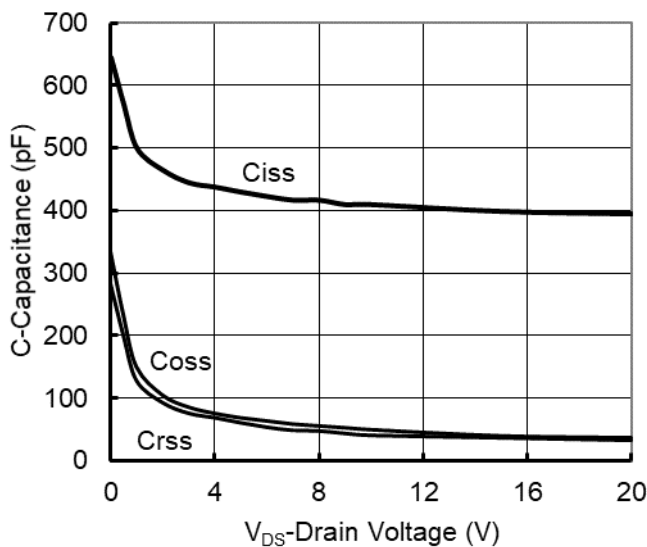


Figure5. Capacitance Characteristics

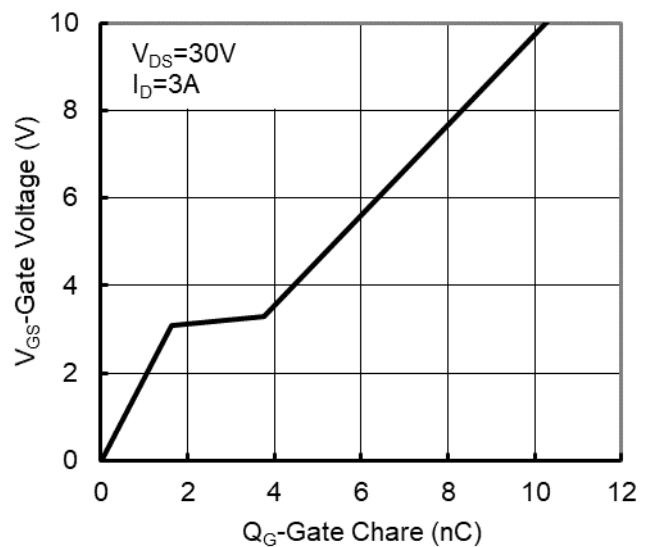


Figure6. Gate Charge



# YJH03N06A

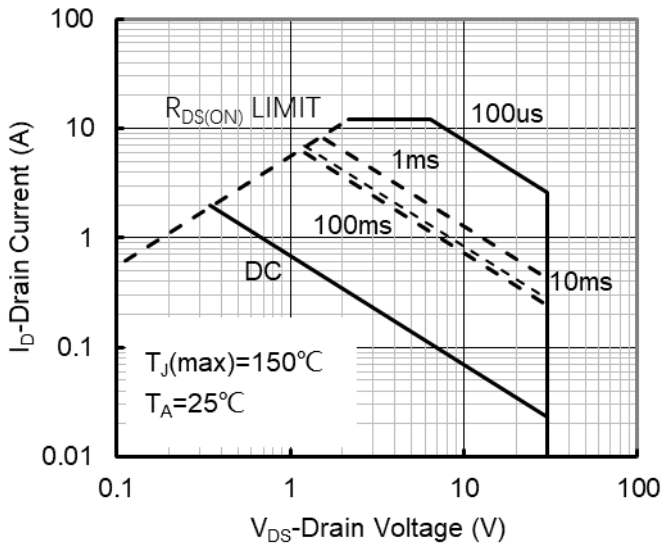


Figure7. Safe Operation Area

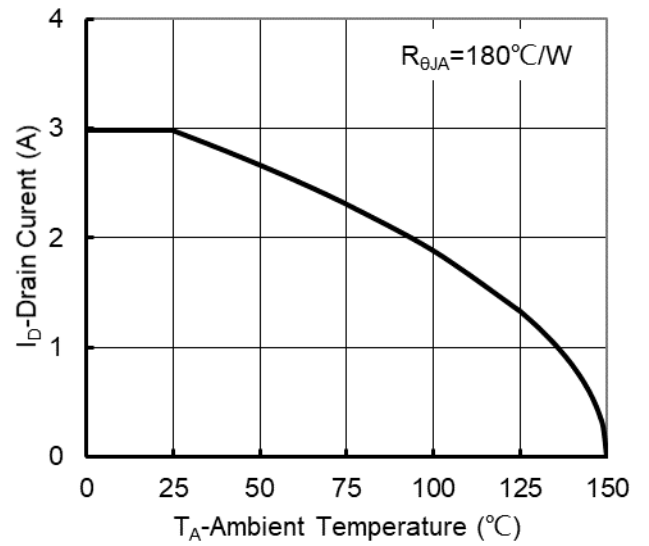


Figure8. Maximum Continuous Drain Current vs Ambient Temperature

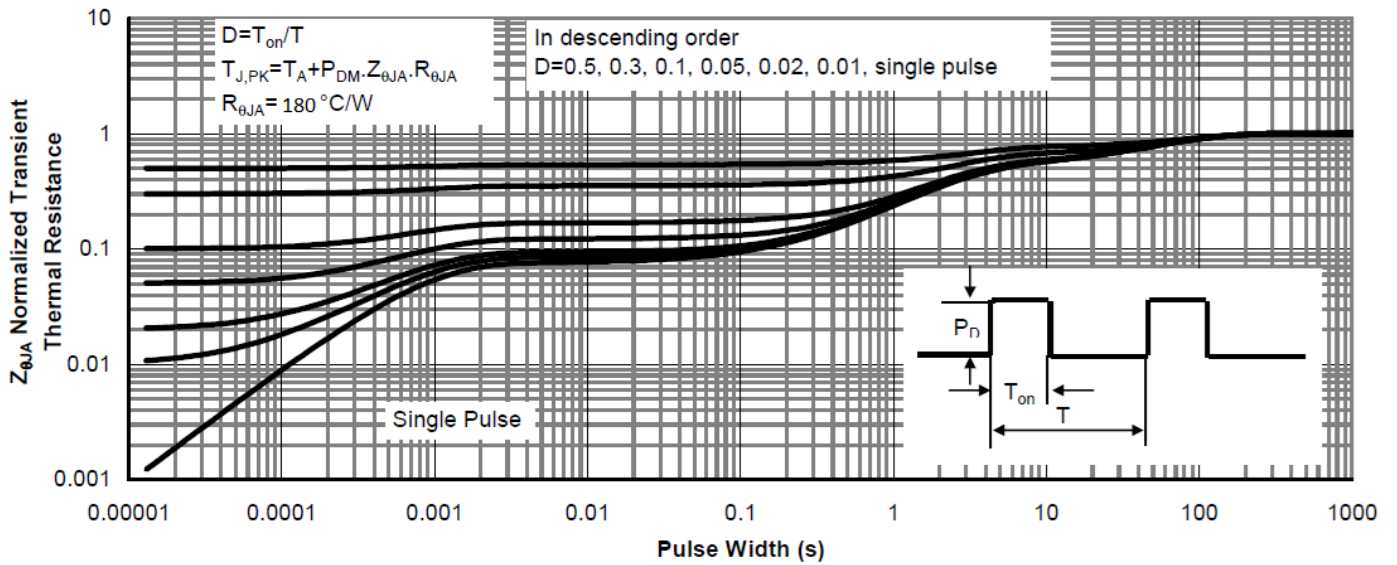
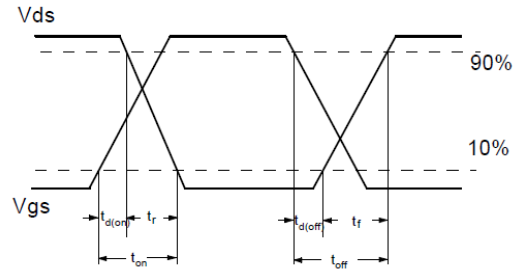
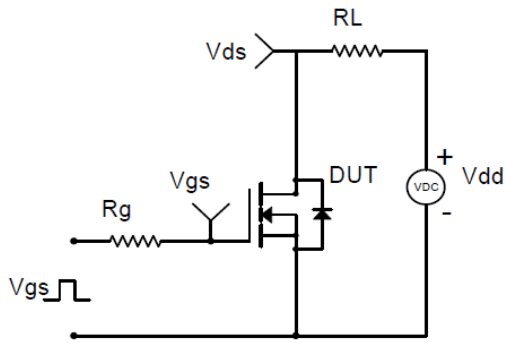
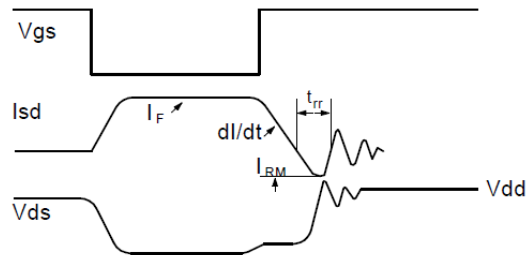
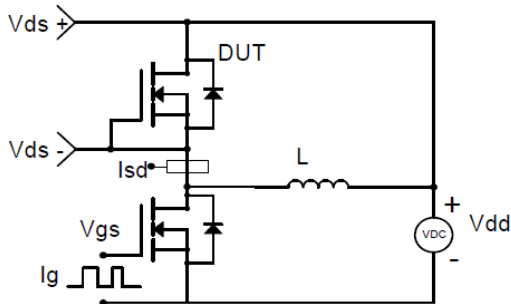


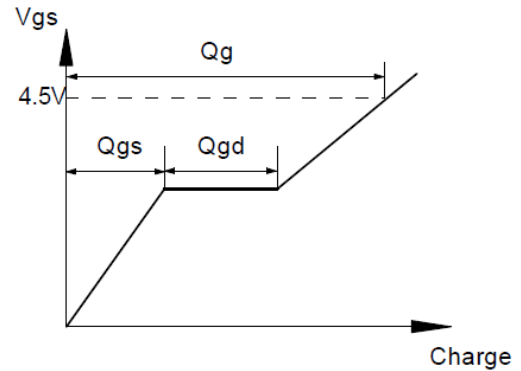
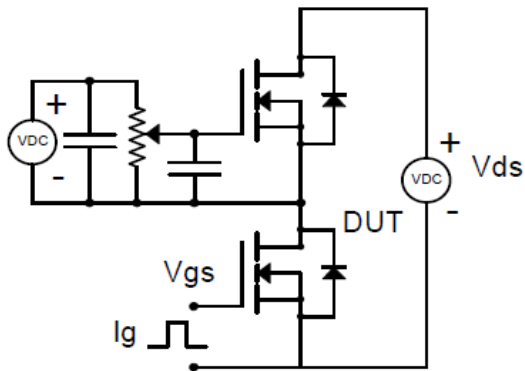
Figure9. Normalized Maximum Transient Thermal Impedance



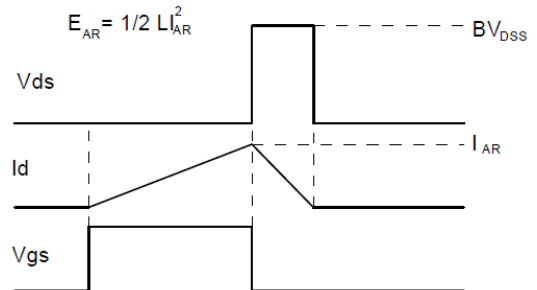
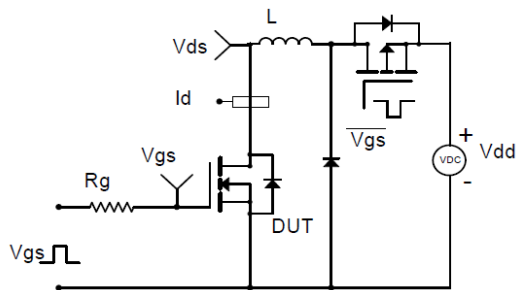
**Resistive Switching Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**



**Gate Charge Test Circuit & Waveform**

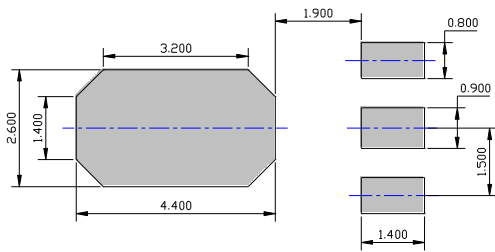
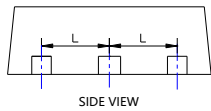
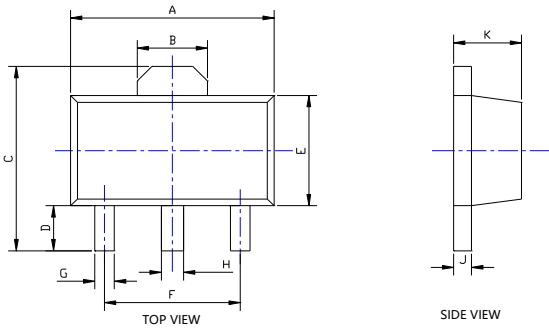


**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**



# YJH03N06A

## ■ SOT-89 Package Information



DIMENSIONS				
DIM	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.169	0.185	4.300	4.700
B	0.061TYP		1.550TYP	
C	0.154	0.171	3.910	4.350
D	0.031	0.047	0.800	1.200
E	0.089	0.104	2.250	2.650
F	0.118TYP		3.000TYP	
G	0.013	0.020	0.330	0.520
H	0.016	0.023	0.400	0.580
J	0.014	0.017	0.350	0.440
K	0.055	0.063	1.400	1.600
L	0.059TYP		1.500TYP	

**NOTE:**

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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